# **HEF4071B**

# Quad 2-input OR gate Rev. 04 — 28 November 2008

**Product data sheet** 

#### **General description** 1.

The HEF4071B is a quad 2-input OR gate. The outputs are fully buffered for highest noise immunity and pattern insensitivity to output impedance variations.

It operates over a recommended  $V_{DD}$  power supply range of 3 V to 15 V referenced to  $V_{SS}$ (usually ground). Unused inputs must be connected to  $V_{\text{DD}},\,V_{\text{SS}},$  or another input. It is also suitable for use over both the industrial (-40 °C to +85 °C) and automotive (-40 °C to +125 °C) temperature ranges.

### 2. Features

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Inputs and outputs are protected against electrostatic effects
- Operates across the automotive temperature range from -40 °C to +125 °C
- Complies with JEDEC standard JESD 13-B
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V

#### 3. Ordering information

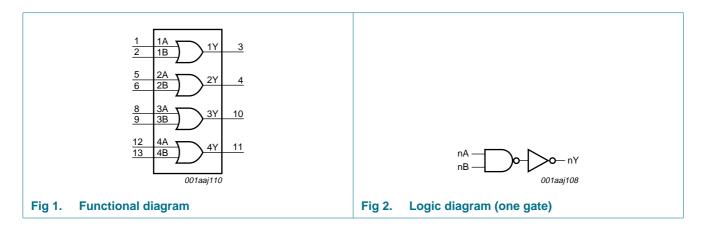
Table 1. **Ordering information** 

All types operate from -40 °C to +125 °C.

Type number	Package							
	Name	Description	Version					
HEF4071BP	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1					
HEF4071BT	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1					

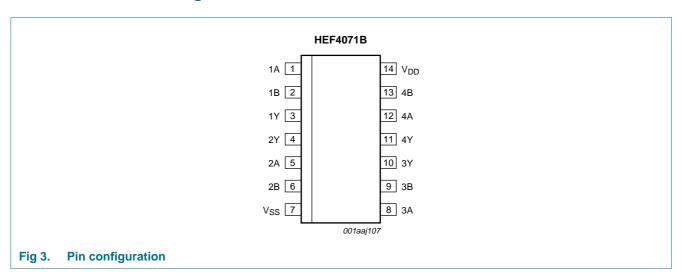


# 4. Functional diagram



# 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 4A	1, 5, 8, 12	input
1B to 4B	2, 6, 9, 13	input
1Y to 4Y	3, 4, 10, 11	output
$V_{SS}$	7	ground (0 V)
$V_{DD}$	14	supply voltage

# 6. Functional description

Table 3. Function table [1]

Input		Output				
nA	nB	nY				
L	L	L				
L	Н	Н				
Н	L	Н				
Н	Н	Н				

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to  $V_{SS} = 0 \text{ V}$  (ground).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DD}$	supply voltage		-0.5	+18	V
I <sub>IK</sub>	input clamping current	$V_{I} < 0.5 \text{ V or } V_{I} > V_{DD} + 0.5 \text{ V}$	-	±10	mΑ
V <sub>I</sub>	input voltage		-0.5	$V_{DD} + 0.5$	V
I <sub>OK</sub>	output clamping current	$V_O < 0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$	-	±10	mA
I <sub>I/O</sub>	input/output current		-	±10	mΑ
$I_{DD}$	supply current		-	50	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>amb</sub>	ambient temperature		-40	+125	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to + 125 } ^{\circ}\text{C}$			
		DIP14	<u>[1]</u> _	750	mW
		SO14	[2] _	500	mW
Р	power dissipation	per output	-	100	mW

<sup>[1]</sup> For DIP14 packages: above  $T_{amb}$  = 70 °C,  $P_{tot}$  derates linearly with 12 mW/K.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DD}$	supply voltage		3	15	V
$V_{I}$	input voltage		0	$V_{DD}$	V
T <sub>amb</sub>	ambient temperature	in free air	-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5 V$	-	3.75	ns/V
		V <sub>DD</sub> = 10 V	-	0.5	ns/V
		V <sub>DD</sub> = 15 V	-	0.08	ns/V

<sup>[2]</sup> For SO14 packages: above  $T_{amb}$  = 70 °C,  $P_{tot}$  derates linearly with 8 mW/K.

# **Static characteristics**

Table 6. **Static characteristics** 

 $V_{SS} = 0 \ V$ ;  $V_I = V_{SS}$  or  $V_{DD}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	$V_{DD}$	T <sub>amb</sub> =	–40 °C	T <sub>amb</sub> = +25 °C		T <sub>amb</sub> = +85 °C		T <sub>amb</sub> = +125 °C		Unit	
				Min	Max	Min	Max	Min	Max	Min	Max		
$V_{IH}$	HIGH-level	$ I_{O}  < 1 \mu A$	5 V	3.5	-	3.5	-	3.5	-	3.5	-	V	
	input voltage		10 V	7.0	-	7.0	-	7.0	-	7.0	-	V	
			15 V	11.0	-	11.0	-	11.0	-	11.0	-	V	
$V_{IL}$	LOW-level	$ I_O  < 1 \mu A$	5 V	-	1.5	-	1.5	-	1.5	-	1.5	V	
	input voltage		10 V	-	3.0	-	3.0	-	3.0	-	3.0	V	
			15 V	-	4.0	-	4.0	-	4.0	-	4.0	V	
$V_{OH}$	HIGH-level	$ I_O  < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V	
	output voltage		10 V	9.95	-	9.95	-	9.95	-	9.95	-	V	
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V	
$V_{OL}$	LOW-level	$ I_O  < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V	
I <sub>OH</sub>	HIGH-level	$V_0 = 2.5 \text{ V}$	5 V	-1.7	-	-1.4	-	-1.1	-	-1.1	-	mΑ	
	output current	output current	$V_0 = 4.6 \text{ V}$	5 V	-0.64	-	-0.5	-	-0.36	-	-0.36	-	mΑ
		$V_0 = 9.5 V$	10 V	-1.6	-	-1.3	-	-0.9	-	-0.9	-	mΑ	
		$V_0 = 13.5 \text{ V}$	15 V	-4.2	-	-3.4	-	-2.4	-	-2.4	-	mΑ	
$I_{OL}$	LOW-level	$V_O = 0.4 V$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mΑ	
	output current	$V_O = 0.5 V$	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mΑ	
		$V_0 = 1.5 \text{ V}$	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mΑ	
l <sub>l</sub>	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μΑ	
$I_{DD}$	supply current	all valid input	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μΑ	
		combinations;	10 V	-	0.5	-	0.5	-	15.0	-	15.0	μΑ	
		$I_O = 0 A$	15 V	-	1.0	-	1.0	-	30.0	-	30.0	μΑ	
C <sub>I</sub>	input capacitance			-	-	-	7.5	-	-	-	-	pF	

5 of 11

# 10. Dynamic characteristics

Table 7. Dynamic characteristics

T<sub>amb</sub> = 25 °C; waveforms see Figure 4; test circuit see Figure 5; unless otherwise specified. [1]

				<del></del>				
Symbol	Parameter	Conditions	$V_{DD}$	Extrapolation formula	Min	Тур	Max	Unit
$t_{PHL}$	HIGH to LOW	nA or nB to nY	5 V	$28 + 0.55 \times C_L$	-	55	115	ns
	propagation delay		10 V	$15 + 0.23 \times C_L$	-	25	50	ns
			15 V	$12 + 0.16 \times C_L$	-	20	35	ns
t <sub>PLH</sub>	LOW to HIGH	nA or nB to nY y	5 V	$18 + 0.55 \times C_L$	-	45	90	ns
	propagation delay		10 V	$9 + 0.23 \times C_L$	-	20	45	ns
			15 V	$7 + 0.16 \times C_L$	-	15	30	ns
t <sub>t</sub>	transition time		5 V	[2] 10 + 1.0 × C <sub>L</sub>	-	60	120	ns
			10 V	$9 + 0.42 \times C_L$	-	30	60	ns
			15 V	$6 + 0.28 \times C_L$	-	20	40	ns
				_				

<sup>[1]</sup> The typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C<sub>L</sub> in pF).

Table 8. Dynamic power dissipation

 $V_{SS} = 0 \text{ V; } t_r = t_f \le 20 \text{ ns; } T_{amb} = 25 \,^{\circ}\text{C.}$ 

Symbol	Parameter	$V_{DD}$	Typical formula	where:
$P_D$	dynamic power dissipation	5 V	$P_D = 1150 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	$f_i$ = input frequency in MHz;
		10 V	$P_D = 4800 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	fo = output frequency in MHz;
		15 V	$P_D = 19700 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	$C_L$ = output load capacitance in pF;
				$\Sigma(f_0 \times C_L)$ = sum of the outputs;
				$V_{DD}$ = supply voltage in V.

### 11. Waveforms

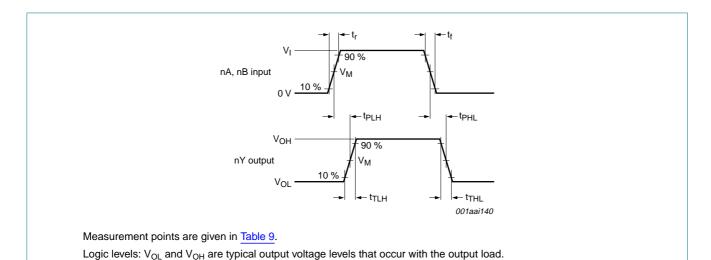


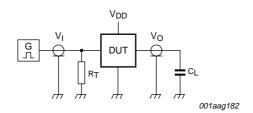
Fig 4. Input to output propagation delay and output transition times

<sup>[2]</sup>  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .



Table 9. Measurement points

Supply voltage	Input	Output
$V_{DD}$	V <sub>M</sub>	V <sub>M</sub>
5 V to 15 V	0.5V <sub>DD</sub>	0.5V <sub>DD</sub>



Test data is given in Table 10.

Definitions for test circuit:

DUT = Device Under Test.

C<sub>L</sub> = load capacitance including jig and probe capacitance.

 $R_T$  = termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

Fig 5. Test circuit

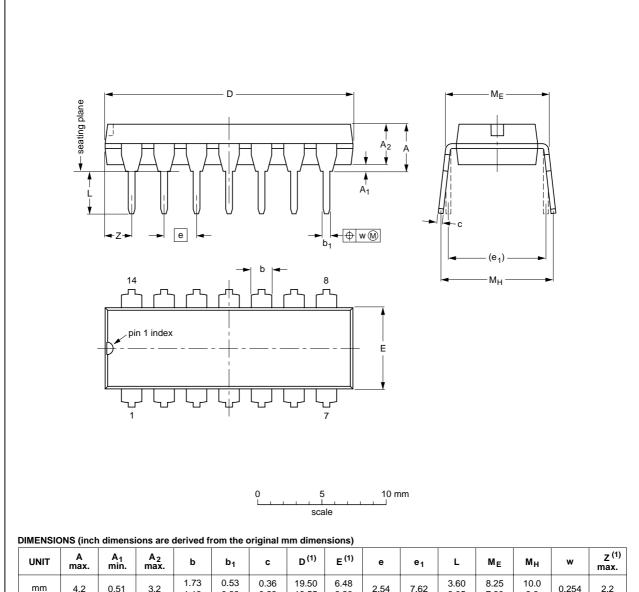
#### Table 10. Test data

Supply voltage	Input	Load	
$V_{DD}$	VI	CL	
5 V to 15 V	V <sub>SS</sub> or V <sub>DD</sub>	≤ 20 ns	50 pF

# 12. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	e <sub>1</sub>	L	ME	Мн	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

### Note

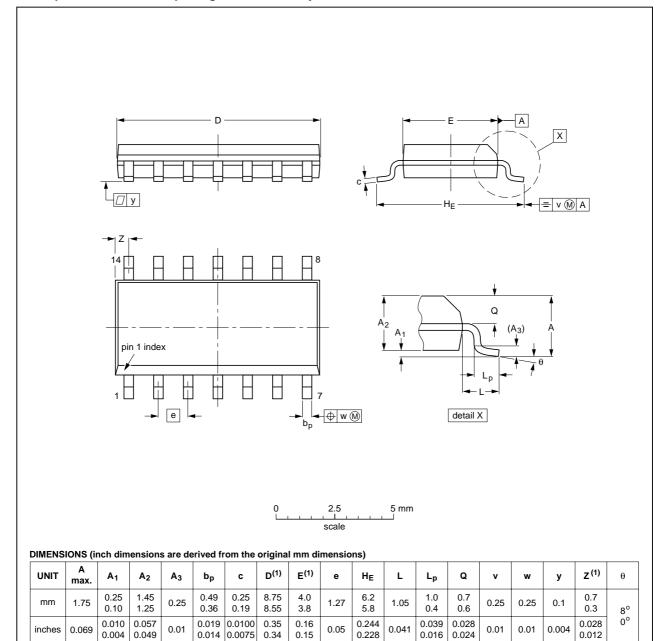
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	1990E DATE	
SOT27-1	050G04	MO-001	SC-501-14		<del>99-12-27</del> 03-02-13	

Package outline SOT27-1 (DIP14) Fig 6.

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	IOOUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19

Fig 7. Package outline SOT108-1 (SO14)

# 13. Abbreviations

### Table 11. Abbreviations

Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

# 14. Revision history

### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
HEF4071B_4	20081128	Product data sheet	-	HEF4071B_CNV_3		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>					
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
	<ul> <li>Temperature range maximum increased from 85 °C to 125 °C throughout the data sheet.</li> </ul>					
	<ul> <li>Section 1 "General description" voltage and temperature range statement added.</li> </ul>					
	Section 2 "Features" added.					
	<ul> <li>Package SOT73 removed from <u>Section 3 "Ordering information"</u> and <u>Section 12 "Package outline"</u>.</li> </ul>					
	<ul> <li>Section 5.2 "Pin description" added.</li> </ul>					
	operating co			Section 8 "Recommended ed, taken from the HE4000B		
	<ul> <li>Section 9 "Static characteristics" I<sub>OH</sub>, I<sub>OL</sub>, I<sub>I</sub> and I<sub>DD</sub> values updated.</li> </ul>					
	<ul> <li>Section 10 "Dynamic characteristics" t<sub>THL</sub> and t<sub>TLH</sub> combined in t<sub>t</sub>.</li> </ul>					
	Section 13 "A	Abbreviations" added.				
HEF4071B_CNV_3	19950101	Product specification	-	HEF4071B_CNV_2		
HEF4071B_CNV_2	19950101	Product specification	-	-		

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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